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AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A light emitting apparatus, comprising:

a light emitting element with an emission wavelength in a range of 360 to 550 nm; and

a rare-earth element doped oxide nitride phosphor,

wherein a part of light radiated from the light emitting element is wavelength-converted by the phosphor, and the phosphor comprises a sialon system phosphor powder comprising α -sialon of 40 weight% or more and 90 weight% or less, the α -sialon being structured such that a Ca site of Ca- α -sialon represented by

$$(Ca_x, M_y)(Si, Al)_{12}(O,N)_{16}$$

is partially replaced by metal (M), β -sialon of 40 weight% or less, and unreacted silicon nitride of and 30 weight% or less, where M comprises metal that is one or more selected from Ce, Pr, Eu, Tb, Yb and Er and 0.05 < (x + y) < 0.3, 0.02 < x < 0.27 and 0.03 < y < 0.3.

2. (Previously presented) The light emitting apparatus according to claim 1, wherein:

the emission wavelength is in the range of 450 to 550 nm; and

the light emitting apparatus radiates white light generated by a mixture of the wavelength-converted light and an other part of light radiated from the light emitting element.

3. (Previously presented) The light emitting apparatus according to claim 1, wherein: the oxide nitride phosphor comprises an oxide nitride that contains the α -sialon as

a matrix material.

- 4. (Previously presented) The light emitting apparatus according to claim 1, wherein: the phosphor comprises a powder or particles and is contained in a light transmitting material.
- 5. (Previously presented) The light emitting apparatus according to claim 1, wherein: the light emitting element comprises a III group nitride system compound semiconductor emitting element.

6-12. (Canceled)

13. (Previously presented) The light emitting apparatus according to claim 1, wherein: the entire phosphor powder has a chemical composition that is in the range of three composition lines of Si_3N_4 -a($M_2O_3\cdot 9AlN$), Si_3N_4 -b($CaO\cdot 3AlN$) and Si_3N_4 -c($AlN\cdot Al_2O_3$), where

$$4 \times 10^{-3} < a < 4 \times 10^{-2}$$
, $8 \times 10^{-3} < b < 8 \times 10^{-2}$ and $10^{-2} < c < 8 \times 10^{-1}$ are satisfied.

14. (Currently amended) A light emitting apparatus, comprising:

a light emitting element with an emission wavelength in the range of 360 to 550 nm; and

a cerium ion doped lanthanum silicon nitride phosphor,
wherein a part of light radiated from the light emitting element is wavelength-

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converted by the phosphor,

a doping amount x is 0.0 < x < 0.2, and the phosphor comprises an electron beam excitation phosphor.

15. (Previously presented) The light emitting apparatus according to claim 14, wherein: the phosphor is represented by:

 $La_{1-x}Si_3N_5$:xCe, where doping amount x is 0 < x < 1, and cerium ion is doped to a lanthanum site in a solid dissolution replacement.

- 16. (Previously presented) The light emitting apparatus according to claim 14, wherein: a doping amount x is 0.1 < x < 0.5, and the phosphor comprises an ultraviolet ray excitation phosphor.
- 17. (Canceled)
- 18. (Original) The light emitting apparatus according to claim 14, wherein: the phosphor radiates blue light.
- 19. (Previously presented) A light emitting method for a light emitting apparatus that comprises a light emitting element with an emission wavelength in a range of 360 to 550 nm and a rare-earth element doped oxide nitride phosphor, wherein a part of light radiated from the light emitting element is wavelength-converted by the phosphor, the phosphor comprises a sialon system phosphor powder comprising α-sialon of 40 weight% or more and

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90 weight% or less, the α -sialon being structured such that a Ca site of Ca- α -sialon represented by

$$(Ca_x, M_y)(Si, Al)_{12}(O,N)_{16}$$

is partially replaced by metal (M), β -sialon of 40 weight% or less, and unreacted silicon nitride of and 30 weight% or less, where M comprises metal that is one or more selected from Ce, Pr, Eu, Tb, Yb and Er and 0.05 < (x + y) < 0.3, 0.02 < x < 0.27 and 0.03 < y < 0.3, and the light emitting apparatus radiates light generated by a mixture of wavelength-converted light and an other part of light radiated from the light emitting element, comprising:

turning on intermittently the light emitting element.

20. (Previously presented) A light emitting method for a light emitting apparatus that comprises a light emitting element with an emission wavelength in a range of 360 to 550 nm and a cerium ion doped lanthanum silicon nitride phosphor, wherein a part of light radiated from the light emitting element is wavelength-converted by the phosphor, a doping amount x is 0.0 < x < 0.2, the phosphor comprises an electron beam excitation phosphor, and the light emitting apparatus radiates light generated by a mixture of wavelength-converted light and an other part of light radiated from the light emitting element, comprising:

turning on intermittently the light emitting.

21. (Previously presented) The light emitting method according to claim 19, wherein: a color of the light radiated from the light emitting apparatus is adjusted by controlling a turn-on time of the light emitting element.

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- 22. (Previously presented) The light emitting method according to claim 20, wherein:
 a color of the light radiated from the light emitting apparatus is adjusted by
 controlling a turn-on time of the light emitting element.
- 23. (Previously presented) The light emitting method according to claim 19, wherein: the emission wavelength is in the range of 450 to 550 nm, and the light emitting apparatus radiates white light.
- 24. (Previously presented) The light emitting method according to claim 20, wherein: the emission wavelength is in the range of 450 to 550 nm, and the light emitting apparatus radiates white light.
- 25. (Previously presented) The light emitting apparatus according to claim 19, wherein: the light emitting element comprises a III group nitride system compound semiconductor emitting element.
- 26. (Previously presented) The light emitting apparatus according to claim 20, wherein:
 the light emitting element comprises a III group nitride system compound
 semiconductor emitting element.
- 27. (New) A light emitting apparatus, comprising:a light emitting element with an emission wavelength in a range of 360 to 550 nm;

a rare-earth element doped oxide nitride phosphor,

wherein a part of light radiated from the light emitting element is wavelength-converted by the phosphor, and the phosphor comprises a sialon system phosphor powder comprising α -sialon of 40 weight% or more and 90 weight% or less, the α -sialon being structured such that a Ca site of Ca- α -sialon represented by

$$(Ca_x, M_y)(Si, Al)_{12}(O,N)_{16}$$

is partially replaced by metal (M), β -sialon of 5 weight% or more and 40 weight% or less, and unreacted silicon nitride of 5 weight% or more and 30 weight% or less, where M comprises metal that is one or more selected from Ce, Pr, Eu, Tb, Yb and Er and 0.05 < (x + y) < 0.3, 0.02 < x < 0.27 and 0.03 < y < 0.3.